## P-Channel 30-V (D-S) MOSFET

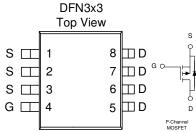
These miniature surface mount MOSFETs utilize a high cell density trench process to provide low  $r_{DS(on)}$  and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

| • | Low $r_{DS(on)}  provides  higher  efficiency  and $ |
|---|--|
|   | extends battery life                                 |

- Low thermal impedance copper leadframe DFN3x3-8PP saves board space
- Fast switching speed

| PRODUCT SUMMARY |                              |            |  |  |  |
|-----------------|------------------------------|------------|--|--|--|
| $V_{DS}(V)$     | $r_{DS(on)} m(\Omega)$       | $I_{D}(A)$ |  |  |  |
| 20              | $60 @ V_{GS} = -10V$         | -5.9       |  |  |  |
| -30             | 90 @ V <sub>GS</sub> = -4.5V | -4.8       |  |  |  |





| High performance trench technology | 1111           |
|------------------------------------|----------------|
| BSOLUTE MAXIMUM RATINGS (TA :      | = 25 °C UNLESS |

| ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25 °C UNLESS OTHERWISE NOTED) |                                     |                                   |            |       |  |  |
|--|-------------------------------------|-----------------------------------|------------|-------|--|--|
| Parameter  |                                     |                                   | Maximum    | Units |  |  |
| Drain-Source Voltage   |                                     |                                   | -30        | V     |  |  |
| Gate-Source Voltage  |                                     |                                   | ±20        | V     |  |  |
|  | $T_A=25^{\circ}C$                   |                                   | -5.9       |       |  |  |
| Continuous Drain Current <sup>a</sup>                                    | $T_A=25^{\circ}C$ $T_A=70^{\circ}C$ | ID                                | -4.8       | A     |  |  |
| Pulsed Drain Current <sup>b</sup>  |                                     |                                   | ±50        |       |  |  |
| Continuous Source Current (Diode Conduction) <sup>a</sup>                |                                     | $I_S$                             | -2.1       | A     |  |  |
| D  | $T_A=25^{\circ}C$                   | D                                 | 3.1        | W     |  |  |
| Power Dissipation <sup>a</sup>   | $T_A=25^{\circ}C$ $T_A=70^{\circ}C$ | $P_{\rm D}$                       | 2.0        | VV    |  |  |
| Operating Junction and Storage Temperature Range                         |                                     | T <sub>J</sub> , T <sub>stg</sub> | -55 to 150 | °C    |  |  |

| THERMAL RESISTANCE RATINGS               |              |                 |       |      |  |  |
|--|--------------|-----------------|-------|------|--|--|
| Parameter                                | Symbol       | Maximum         | Units |      |  |  |
| a  | t <= 10 sec  | ъ               | 35    | °C/W |  |  |
| Maximum Junction-to-Ambient <sup>a</sup> | Steady State | $R_{\theta JA}$ | 81    | °C/W |  |  |

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## Notes

- Surface Mounted on 1" x 1" FR4 Board. a.
- Pulse width limited by maximum junction temperature b.

Analog Power AMCC431P

| SPECIFICATIONS (T <sub>A</sub> = 25°C UNLESS OTHERWISE NOTED) |                     |  |        |      |      |       |  |
|---|---------------------|--|--------|------|------|-------|--|
| Parameter   | Symbol              | Test Conditions  | Limits |      |      | Unit  |  |
| Faianietei  | Symbol              | rest Conditions  | Min    | Тур  | Max  | Oilit |  |
| Static  |                     |  |        |      |      |       |  |
| Gate-Threshold Voltage  | $V_{GS(th)}$        | $V_{DS} = V_{GS}$ , $I_D = -250 \text{ uA}$                                | -1     |      |      | V     |  |
| Gate-Body Leakage   | I <sub>GSS</sub>    | $V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$                          |        |      | ±100 | nA    |  |
| Zero Gate Voltage Drain Current                               | l                   | $V_{DS} = -24 \text{ V}, V_{GS} = 0 \text{ V}$                             |        |      | -1   | uA    |  |
| Zero date voltage brain current                               | I <sub>DSS</sub>    | $V_{DS} = -24 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$ |        |      | -5   |       |  |
| On-State Drain Current <sup>A</sup>                           | I <sub>D(on)</sub>  | $V_{DS}$ = -5 V, $V_{GS}$ = -10 V  | -50    |      |      | Α     |  |
| Drain-Source On-Resistance <sup>A</sup>                       | r <sub>DS(on)</sub> | $V_{GS} = -10 \text{ V}, I_D = -1 \text{ A}$                               |        |      | 60   | mΩ    |  |
| Dialii-Source Ori-nesistance                                  |                     | $V_{GS} = -4.5 \text{ V}, I_D = -1 \text{ A}$                              |        |      | 90   | 11122 |  |
| Forward Tranconductance <sup>A</sup>                          | 9 <sub>fs</sub>     | $V_{DS} = -15 \text{ V}, I_{D} = -1 \text{ A}$                             |        | 29   |      | S     |  |
| Diode Forward Voltage   | $V_{SD}$            | $I_S = 1 A$ , $V_{GS} = 0 V$   |        | -0.8 |      | V     |  |
| Dynamic <sup>b</sup>  |                     |  |        |      |      |       |  |
| Total Gate Charge   | $Q_g$               | $V_{DS} = -15 \text{ V}, V_{GS} = -5 \text{ V},$                           |        | 14   |      |       |  |
| Gate-Source Charge  | $Q_{gs}$            | $V_{DS} = -13 \text{ V}, V_{GS} = -3 \text{ V},$ $I_{D} = -1 \text{ A}$    |        | 4    |      | пC    |  |
| Gate-Drain Charge   | $Q_{gd}$            | I <sub>D</sub> = -1 A  |        | 8    |      | 1     |  |
| Turn-On Delay Time  | t <sub>d(on)</sub>  |  |        | 4    |      |       |  |
| Rise Time   | t <sub>r</sub>      | $V_{DD}$ = -15 V, $R_L$ = 6 $\Omega$ ,                                     |        | 5    |      | nS    |  |
| Turn-Off Delay Time   | t <sub>d(off)</sub> | $I_D = -1 A, V_{GEN} = -10 V$  |        | 80   |      |       |  |
| Fall-Time   | t <sub>f</sub>      |  |        | 40   |      |       |  |

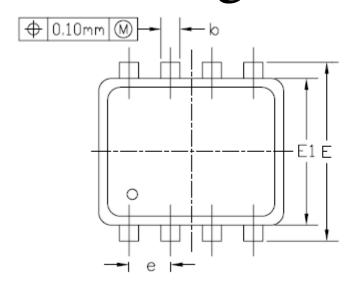
## Notes

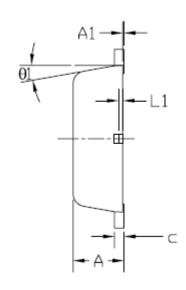
a. Pulse test:  $PW \le 300$ us duty cycle  $\le 2\%$ .

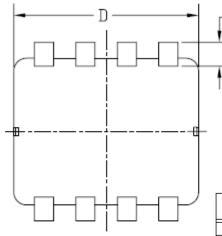
b. Guaranteed by design, not subject to production testing.

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## Package Information







BOTTOM VIEW

| SYMBOLS   | DIMENS   | DIMENSIONS IN MILLIMETERS |      |                  | DIMENSIONS IN INCHES |       |  |
|-----------|----------|---------------------------|------|------------------|----------------------|-------|--|
| 51 MIDULS | MIN      | NOM                       | MAX  | MIN              | NOM                  | MAX   |  |
| A         | 0.70     | 0.80                      | 0.90 | 0.028 0.031 0.03 |                      |       |  |
| A1        | 0.00     |                           | 0.05 | 0.000 — 0.00     |                      |       |  |
| b         | 0.24     | 0.30                      | 0.35 | 0.009            | 0.014                |       |  |
| С         | 0.08     | 0.15                      | 0.25 | 0.003            | 0.006                | 0.010 |  |
| D         | 2.90 BSC |                           |      | 0.114 BSC        |                      |       |  |
| E         | 2.80 BSC |                           |      | 0.110 BSC        |                      |       |  |
| E1        | 2.30 BSC |                           |      | 0.091 BSC        |                      |       |  |
| e         | 0.65 BSC |                           |      | 0.026 BSC        |                      |       |  |
| L         | 0.20     | 0.38                      | 0.45 | 0.008            | 0.015                | 0.018 |  |
| L1        | 0.05     |                           |      | 0.002            |                      |       |  |
| θ1        | 0°       | 10°                       | 12°  | 0°               | 10°                  | 12°   |  |